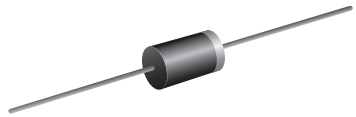
EM1Y - EM1C

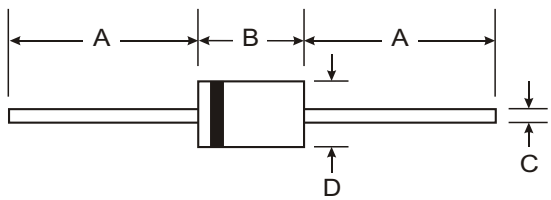
AXIAL LEADED SILICON RECTIFIER DIODES

VOLTAGE RANGE: 100 - 1000V
CURRENT: 1.0 A



Features

- Low cost
- Diffused junction
- Low leakage
- Low forward voltage drop
- High current capability
- Easily cleaned with Freon,Alcohol,Isopropanol and similar solvents
- The plastic material carries U/L recognition 94V-0



DO-41		
Dim	**Min**	**Max**
A	25.40	—
B	4.06	5.21
C	0.71	0.864
D	2.00	2.72
All Dimensions in mm		

Mechanical Data

- Case: D O - 4 1 Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.34 grams (approx.)
- Mounting Position: Any
- Marking: Type Number

RoHS COMPLIANT

Maximum Ratings and Electrical Characteristics

T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	EM1Y	EM1Z	EM1	EM1A	EM1B	EM1C	Unit
Maximum recurrent peak reverse voltage	V_{RRM}	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	100	200	400	600	800	1000	V
Maximum average forw ard rectified current 9.5mm lead length, @T_A=75℃	$I_{F(AV)}$	1.0						A
Peak forw ard surge current 8.3ms single half-sine-w ave superimposed on rated load @T_J=125℃	I_{FSM}	45.0						A
Maximum instantaneous forw ard voltage @ 1.0 A	V_F	0.97						V
Maximum reverse current @T_A=25℃	I_R	5.0						μA
at rated DC blocking voltage @T_A=100℃		50.0						
Typical junction capacitance (Note1)	C_J	15						pF
Typical thermal resistance (Note2)	$R_{\theta JA}$	50						℃/W
Operating junction temperature range	T_J	- 55---- +150						℃
Storage temperature range	T_{STG}	- 55---- + 150						℃

NOTE: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
2. Thermal resistance from junction to ambient.

FIG.1 -- FORWARD DERATING CURVE

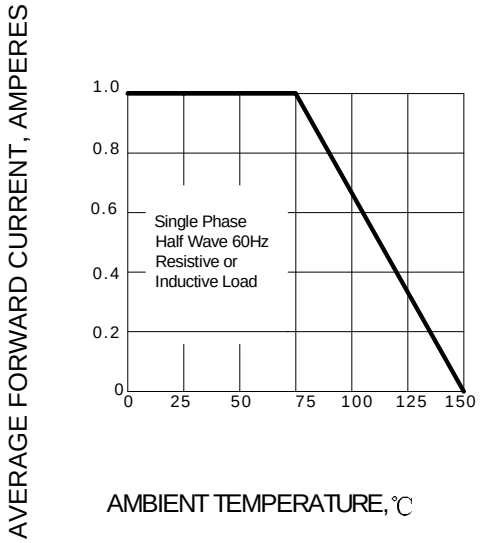


FIG.2 -- TYPICAL FORWARD CHARACTERISTICS

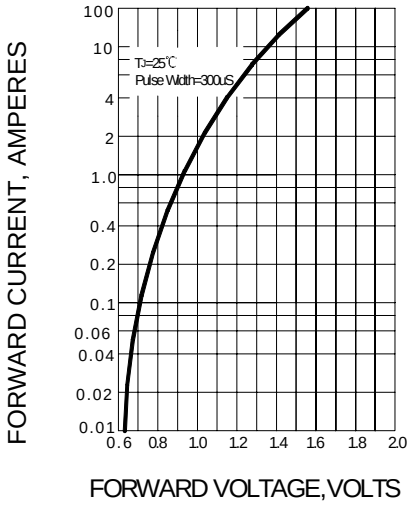


FIG.3 -- PEAK FORWARD SURGE CURRENT

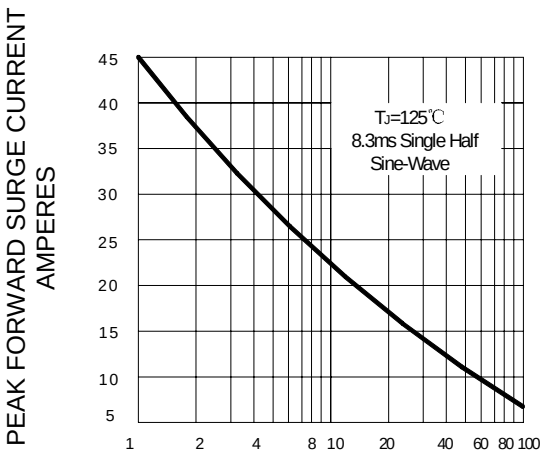


FIG.5--TYPICAL JUNCTION CAPACITANCE

